

# FDB86135

## N-Channel PowerTrench® MOSFET

### 100V, 176A, 3.5mΩ

#### Features

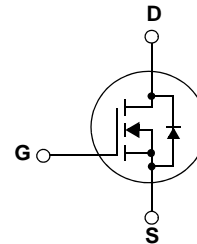
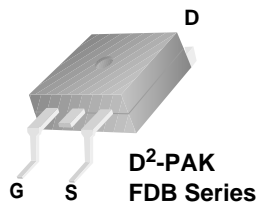
- Max  $R_{DS(on)} = 3.5m\Omega$  at  $V_{GS} = 10V$ ,  $I_D = 75A$
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

#### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

#### Applications

- DC-DC primary bridge
- DC-DC Synchronous rectification
- Hot swap



#### MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units	
$V_{DSS}$	Drain to Source Voltage	100	V	
$V_{GSS}$	Gate to Source Voltage	$\pm 20$	V	
$I_D$	Drain Current - Continuous (Silicon Limited) $T_C = 25^\circ C$	176	A	
	- Continuous (Package Limited) $T_C = 25^\circ C$	120		
	- Continuous $T_C = 25^\circ C$ (Note 1a)	75	A	
	- Pulsed	704		
$E_{AS}$	Single Pulsed Avalanche Energy (Note 3)	658	mJ	
$P_D$	Power Dissipation	- $T_C = 25^\circ C$ (Note 1a)	227	W
		- $T_A = 25^\circ C$ (Note 1b)	2.4	W/ $^\circ C$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ C$	

#### Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	0.66	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	62.5	

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB86135	FDB86135	D2-PAK	330mm	24mm	800

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$ , $T_C = 25^\circ\text{C}$	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.07	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{V}$ , $V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$ , $I_D = 75\text{A}$	-	3.0	3.5	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{V}$ , $I_D = 75\text{A}$	-	167	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	5485	7295	pF
$C_{oss}$	Output Capacitance		-	2430	3230	pF
$C_{rfs}$	Reverse Transfer Capacitance		-	210	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 80\text{V}$ , $I_D = 75\text{A}$ $V_{GS} = 10\text{V}$	-	89	116	nC
$Q_{gs}$	Gate to Source Gate Charge		-	24	-	nC
$Q_{gs2}$	Gate Charge Threshold to Plateau		-	8	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	25	-	nC

### Switching Characteristics

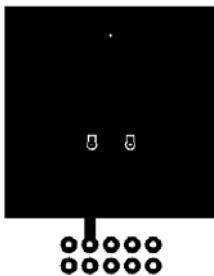
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{V}$ , $I_D = 75\text{A}$ $V_{GS} = 10\text{V}$ , $R_{GEN} = 4.7\Omega$	-	22	54	ns
$t_r$	Turn-On Rise Time		-	54	118	ns
$t_{d(off)}$	Turn-Off Delay Time		-	37	84	ns
$t_f$	Turn-Off Fall Time		-	11	32	ns

### Drain-Source Diode Characteristics

$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_{SD} = 75\text{A}$ (Note 2)	-	-	1.25	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{V}$ , $I_{SD} = 75\text{A}$ , $V_{DD} = 80\text{V}$	-	72	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100\text{A}/\mu\text{s}$	-	129	-	nC

#### NOTES:

- $R_{\theta JA}$  is determined with the device mounted on a  $1\text{ in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{ in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $40^\circ\text{C}/\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $62.5^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width  $< 300\ \mu\text{s}$ , Duty cycle  $< 2.0\%$ .
- Starting  $T_J = 25^\circ\text{C}$ ,  $L = 1\text{ mH}$ ,  $I_{AS} = 36.3\text{ A}$ ,  $V_{DD} = 100\text{ V}$ ,  $V_{GS} = 10\text{ V}$ .

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

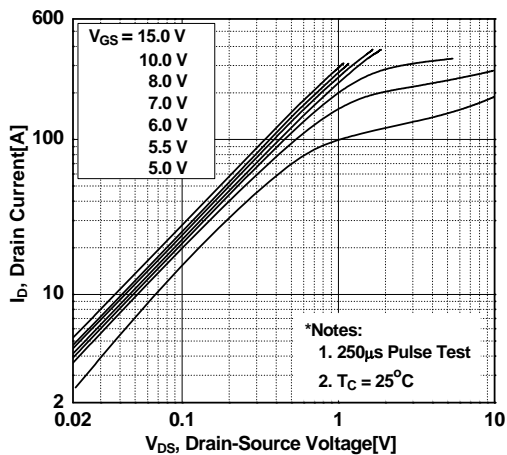


Figure 2. Transfer Characteristics

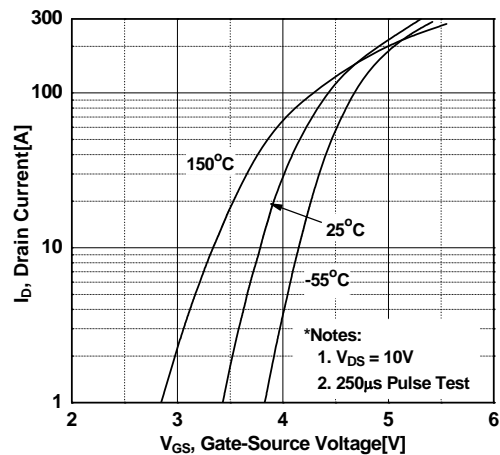


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

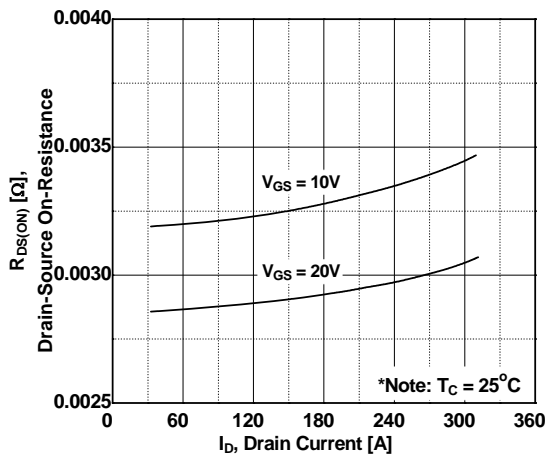


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

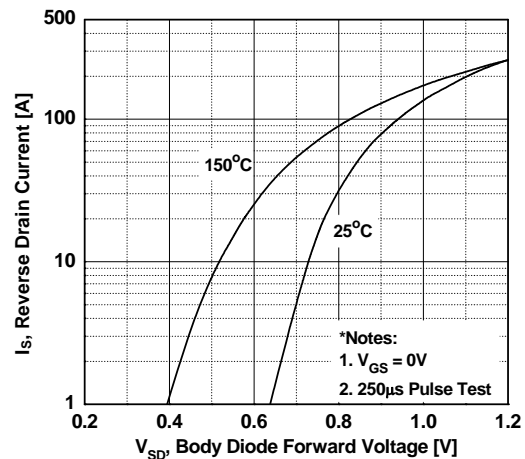


Figure 5. Capacitance Characteristics

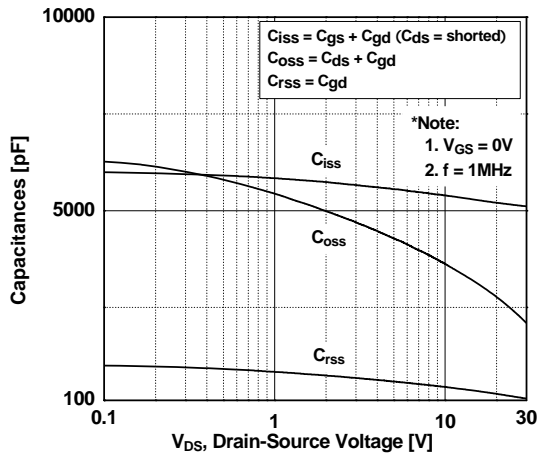
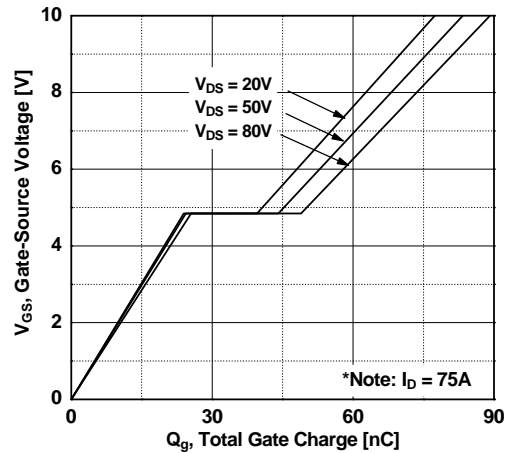
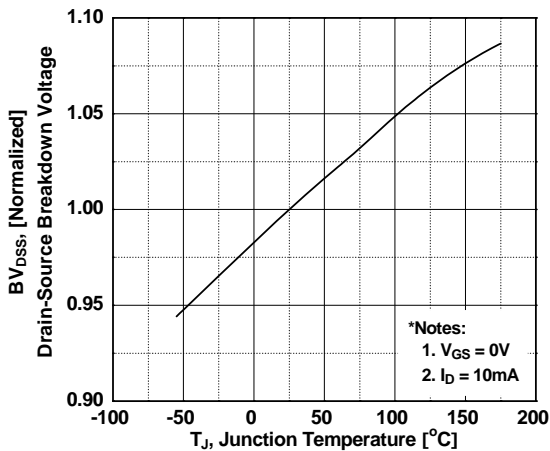


Figure 6. Gate Charge Characteristics

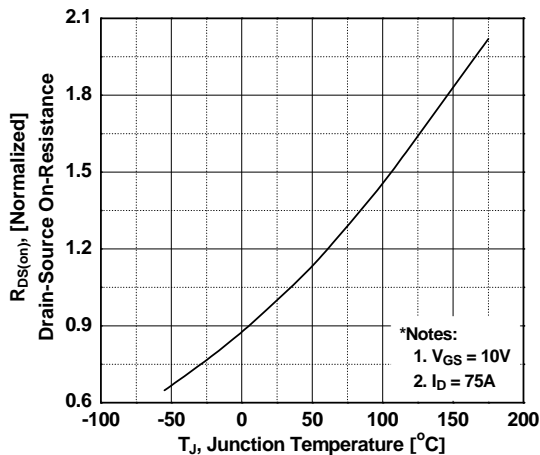


## Typical Performance Characteristics

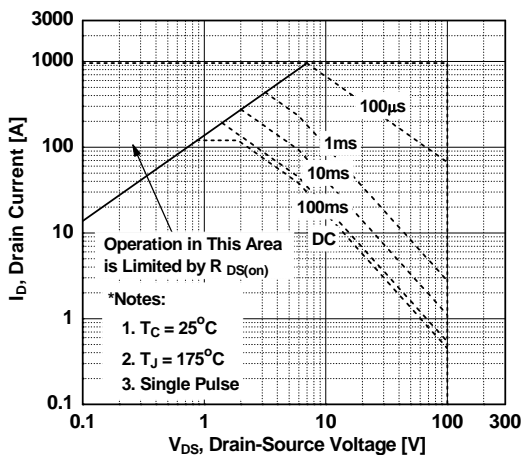
**Figure 7. Breakdown Voltage Variation vs. Temperature**



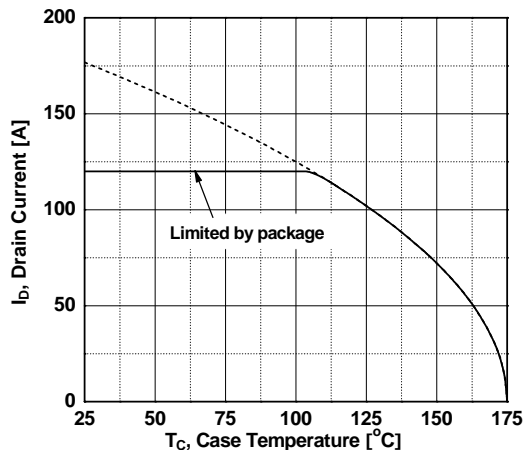
**Figure 8. On-Resistance Variation vs. Temperature**



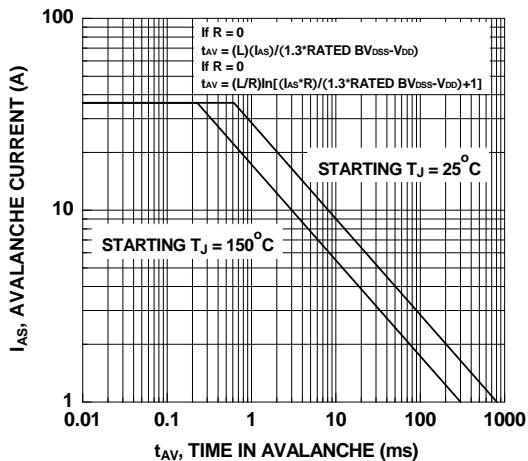
**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**

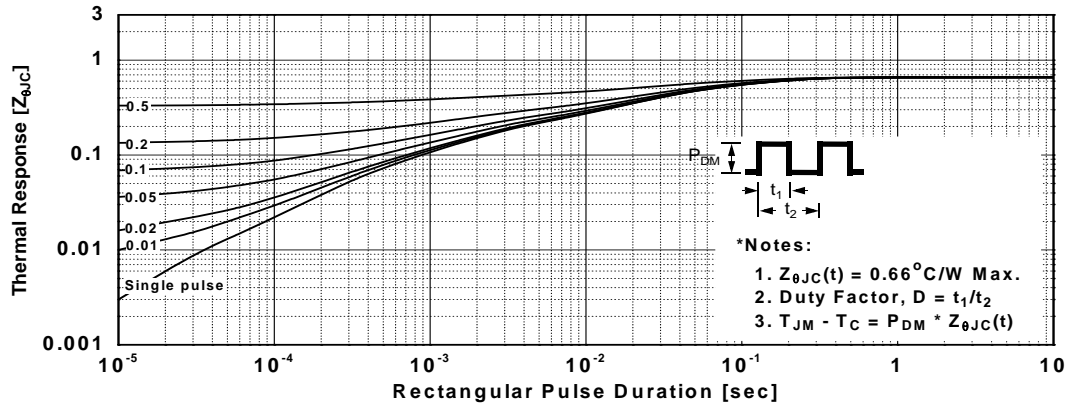


**Figure 11. Unclamped Inductive Switching Capability**

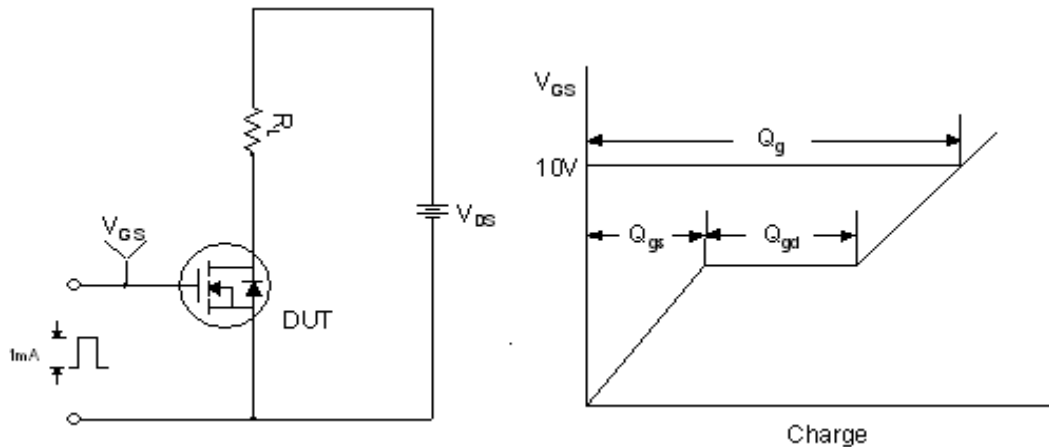


Typical Performance Characteristics

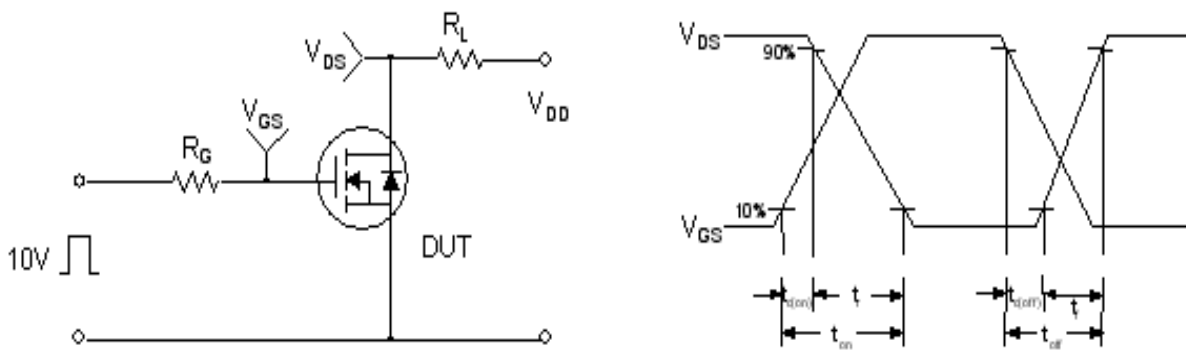
Figure 12. Transient Thermal Response Curve



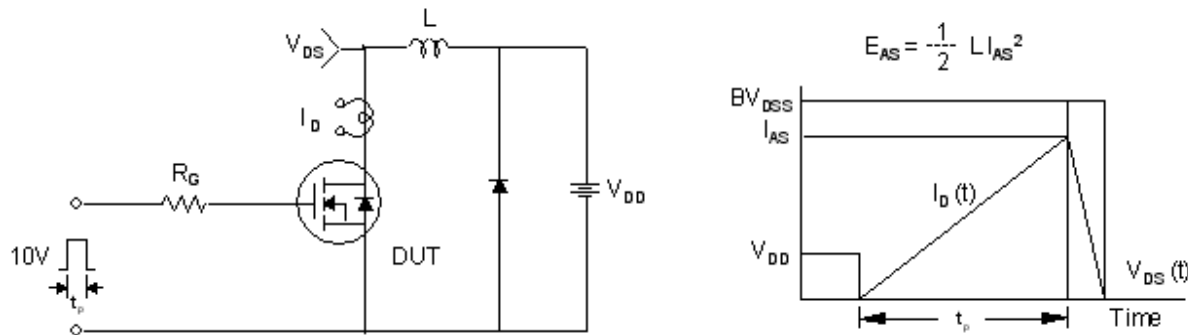
**Gate Charge Test Circuit & Waveform**



**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

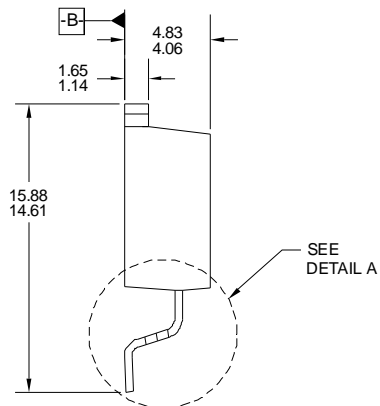
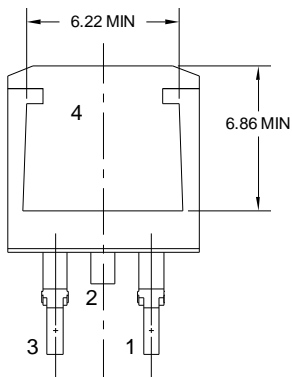
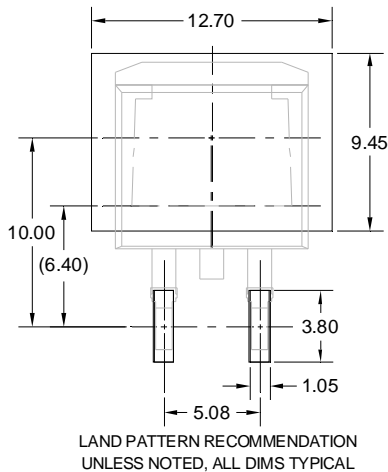
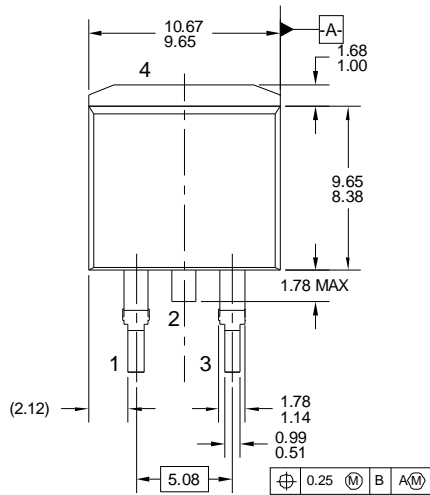


Peak Diode Recovery dv/dt Test Circuit & Waveforms

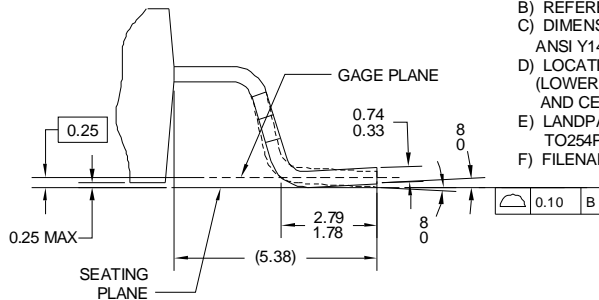


**Mechanical Dimensions**

**D2-PAK**



- NOTES: UNLESS OTHERWISE SPECIFIED  
 A) ALL DIMENSIONS ARE IN MILLIMETERS.  
 B) REFERENCE JEDEC, TO-263, VARIATION AB.  
 C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1994.  
 D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).  
 E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N  
 F) FILENAME: TO263A02REV6



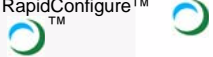




Dimensions in Millimeters





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